

Product data sheet

## 1. General description

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBSS5230QA.

## 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

## 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

## 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	30	V
I <sub>C</sub>	collector current			-	-	2	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	3	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300$ μs; δ $\le 0.02$ ; $T_{amb}$ = 25 °C		-	135	180	mΩ

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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	E	emitter		в
3	С	collector	4 3	<b>N</b>
4	С	collector	Transparent top view DFN1010D-3 (SOT1215)	E sym123

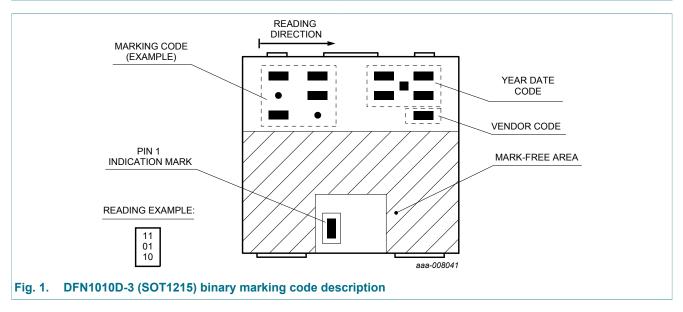
# 6. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
PBSS4230QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS4230QA	01 11 00



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## 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	2	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	3	А
I <sub>B</sub>	base current			-	0.3	А
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

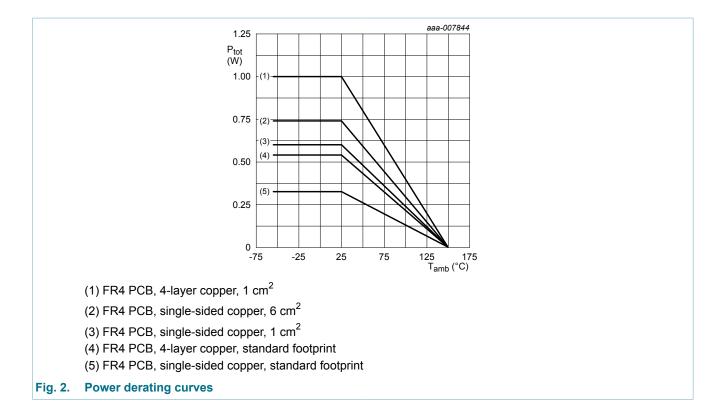
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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## 9. Thermal characteristics

Table 6. T	able 6. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W	
		[2]	-	-	209	K/W	
		[3]	-	-	169	K/W	
		[4]	-	-	232	K/W	
			[5]	-	-	125	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

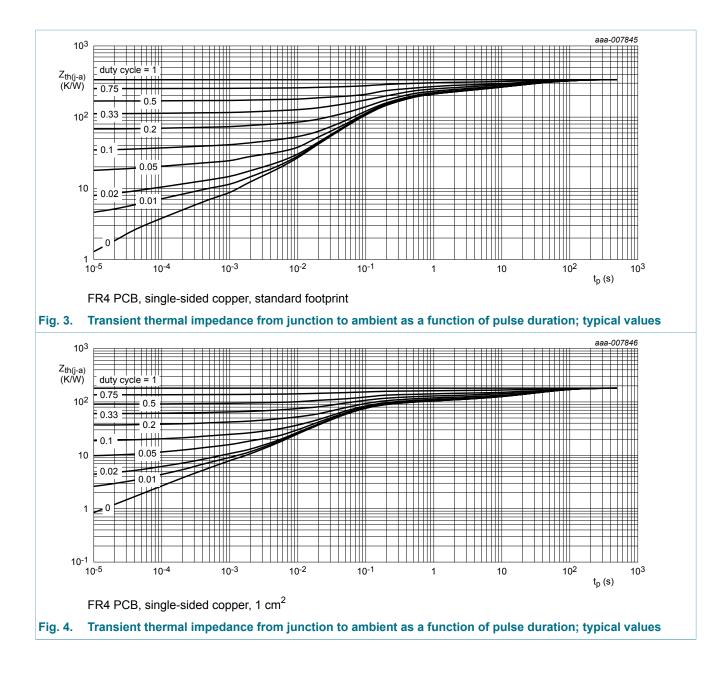
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

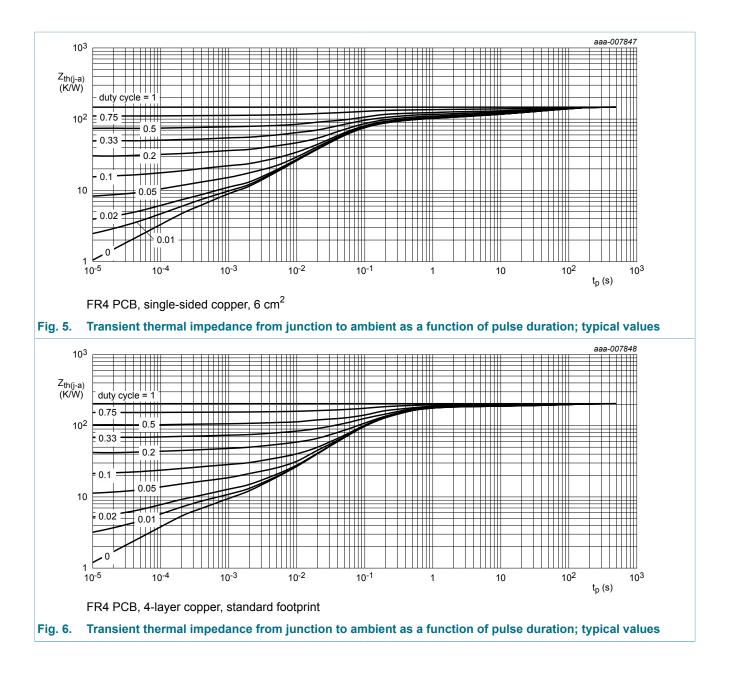


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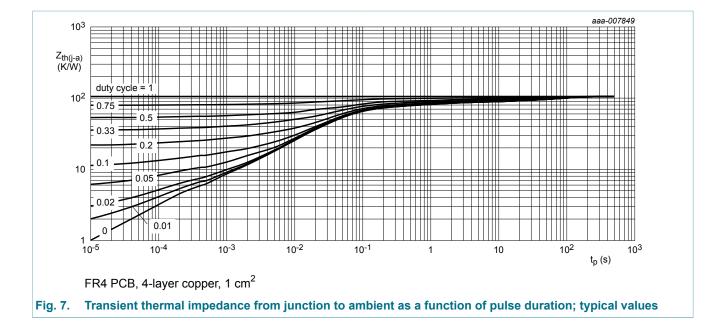
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## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = 24 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 24 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 24 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub> DC current gain	$V_{CE} = 2 \text{ V; } I_C = 100 \text{ mA; pulsed;}$ $t_p \le 300  \mu\text{s}; \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	250	430	-		
		$\begin{split} &V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 500 mA; pulsed;} \\ &t_{p} \texttt{\le 300 \mu s; } \overline{o} \texttt{\le 0.02 ; } T_{amb} \texttt{= 25 °C} \end{split}$	230	380	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \; V; \; I_C = 1 \; A; \; \text{pulsed}; \; t_p \leq 300 \; \mu\text{s}; \\ \bar{\delta} &\leq 0.02 \; ; \; T_{amb} = 25 \; ^\circ\text{C} \end{split}$	180	290	-	
		$V_{CE} = 2 \text{ V; } I_C = 2 \text{ A; pulsed; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	100	160	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	75	100	mV
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	140	190	mV
		$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\overline{\delta} \le 0.02$ ; $T_{amb}$ = 25 °C	-	135	180	mV

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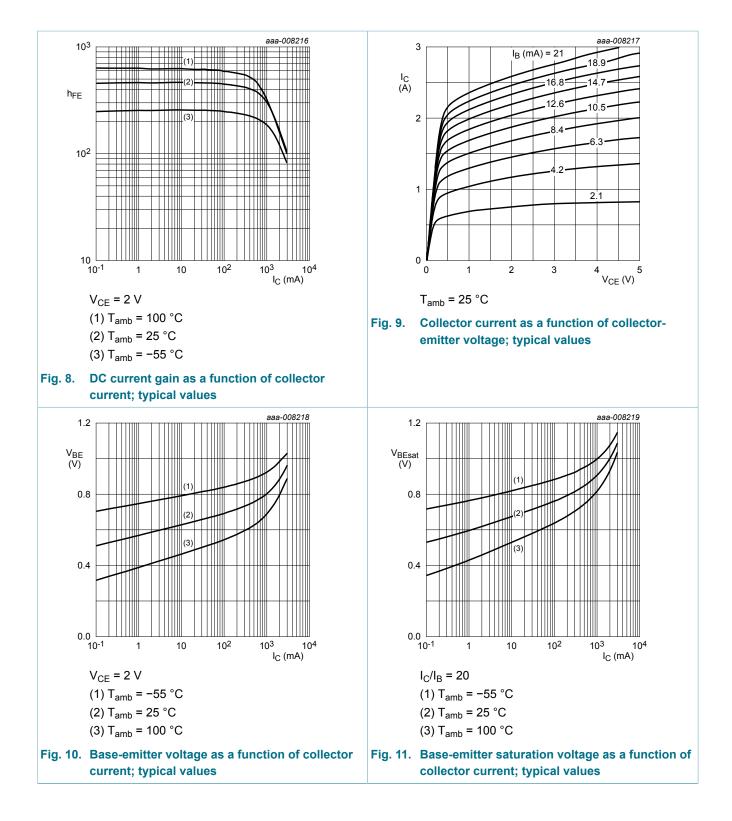
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_{C}$ = 2 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	265	360	mV
		$I_{C}$ = 2 A; $I_{B}$ = 200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	255	350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	135	180	mΩ
V <sub>BEsat</sub> base-emitter saturation voltage		I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	0.86	1	V
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	0.9	1.05	V
	$I_C$ = 2 A; $I_B$ = 100 mA; pulsed; $t_p \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	1	1.15	V	
	$I_{C}$ = 2 A; $I_{B}$ = 200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	1.05	1.2	V	
V <sub>BEon</sub>	base-emitter turn-on voltage	$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \; V; \; I_{C} = 0.5 \; A; \; pulsed; \\ t_{p} \leq 300 \; \mu s; \; \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ} C \end{array}$	-	0.75	0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = 10 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 25 mA;	-	15	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -25 mA; T <sub>amb</sub> = 25 °C	-	30	-	ns
t <sub>on</sub>	turn-on time		-	45	-	ns
t <sub>s</sub>	storage time		-	425	-	ns
t <sub>f</sub>	fall time		-	65	-	ns
t <sub>off</sub>	turn-off time		-	490	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; I <sub>C</sub> = 50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	130	190	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	8	10	pF

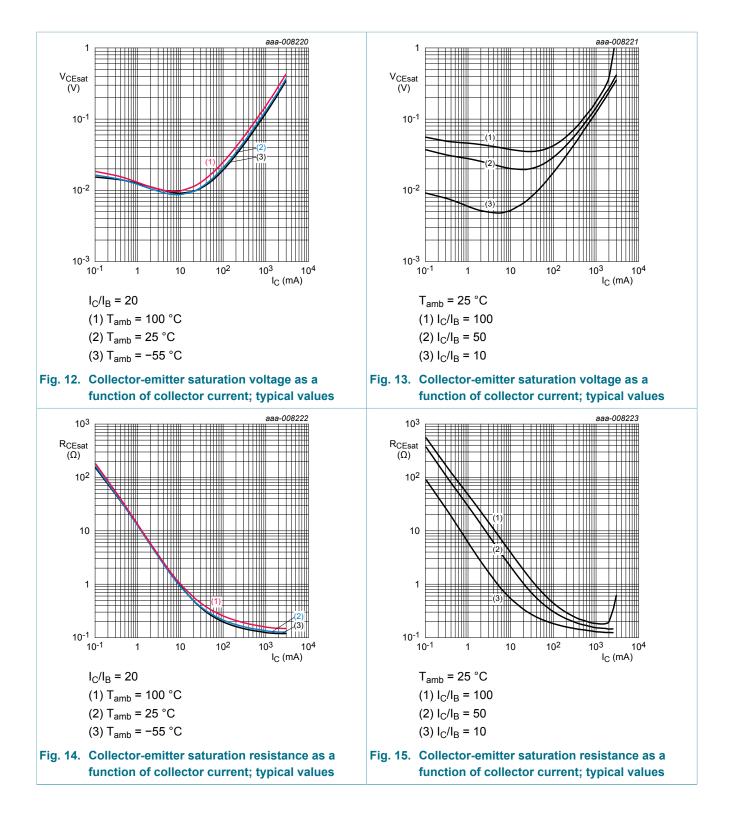
#### 30 V, 2 A NPN low VCEsat (BISS) transistor



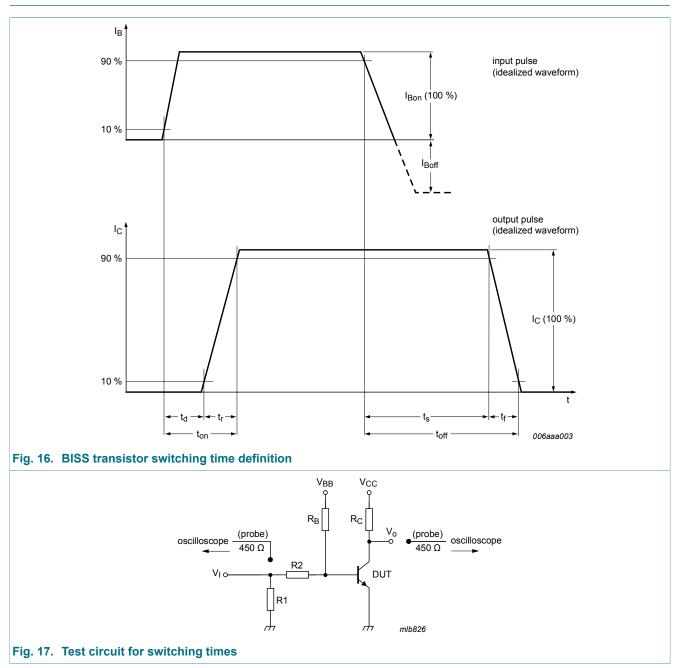
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## 11. Test information

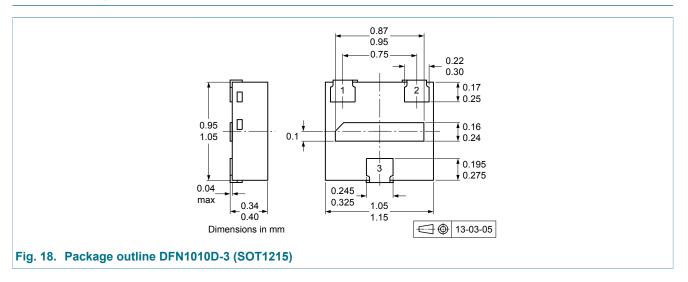
## **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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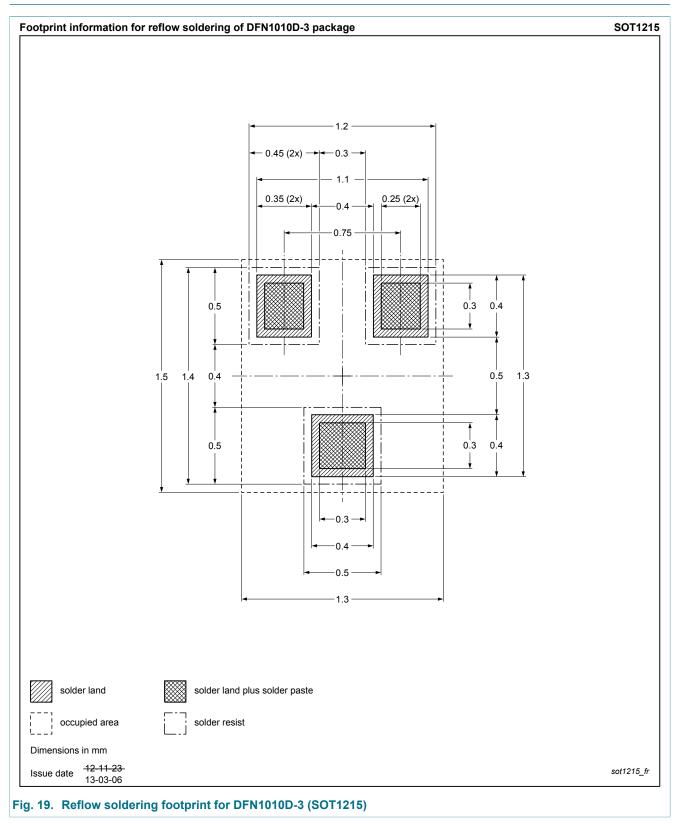
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# 12. Package outline



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## 13. Soldering



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# 14. Revision history

Table 8. Revision history				
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4230QA v.1	20130823	Product data sheet	-	-

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## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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